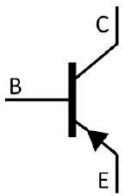


Silicon PNP transistor in a TO-92 Plastic Package.

High voltage.

High voltage control circuit application.

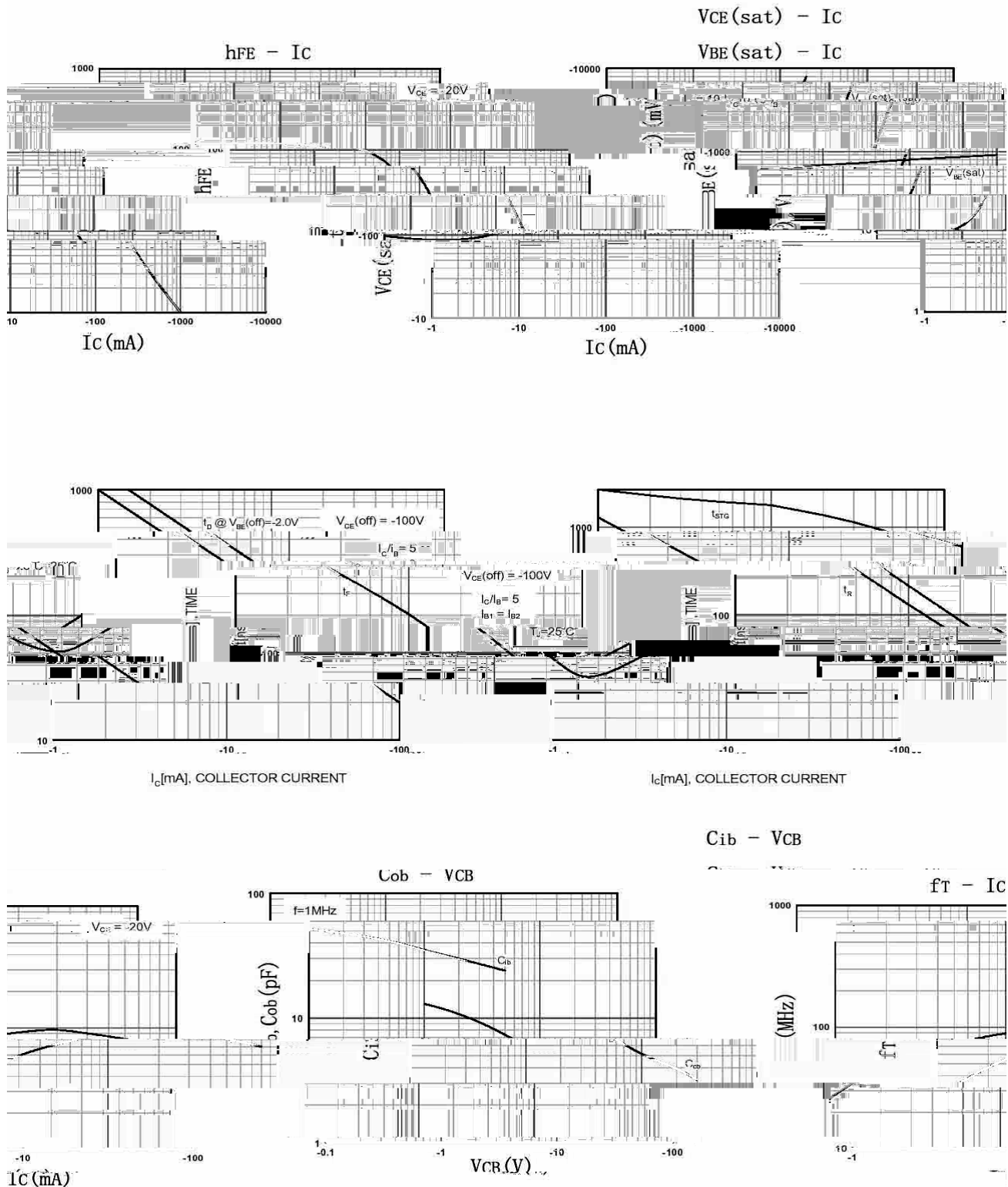


PIN1 Collector PIN 2 Base PIN 3 Emitter

See Marking Instructions.

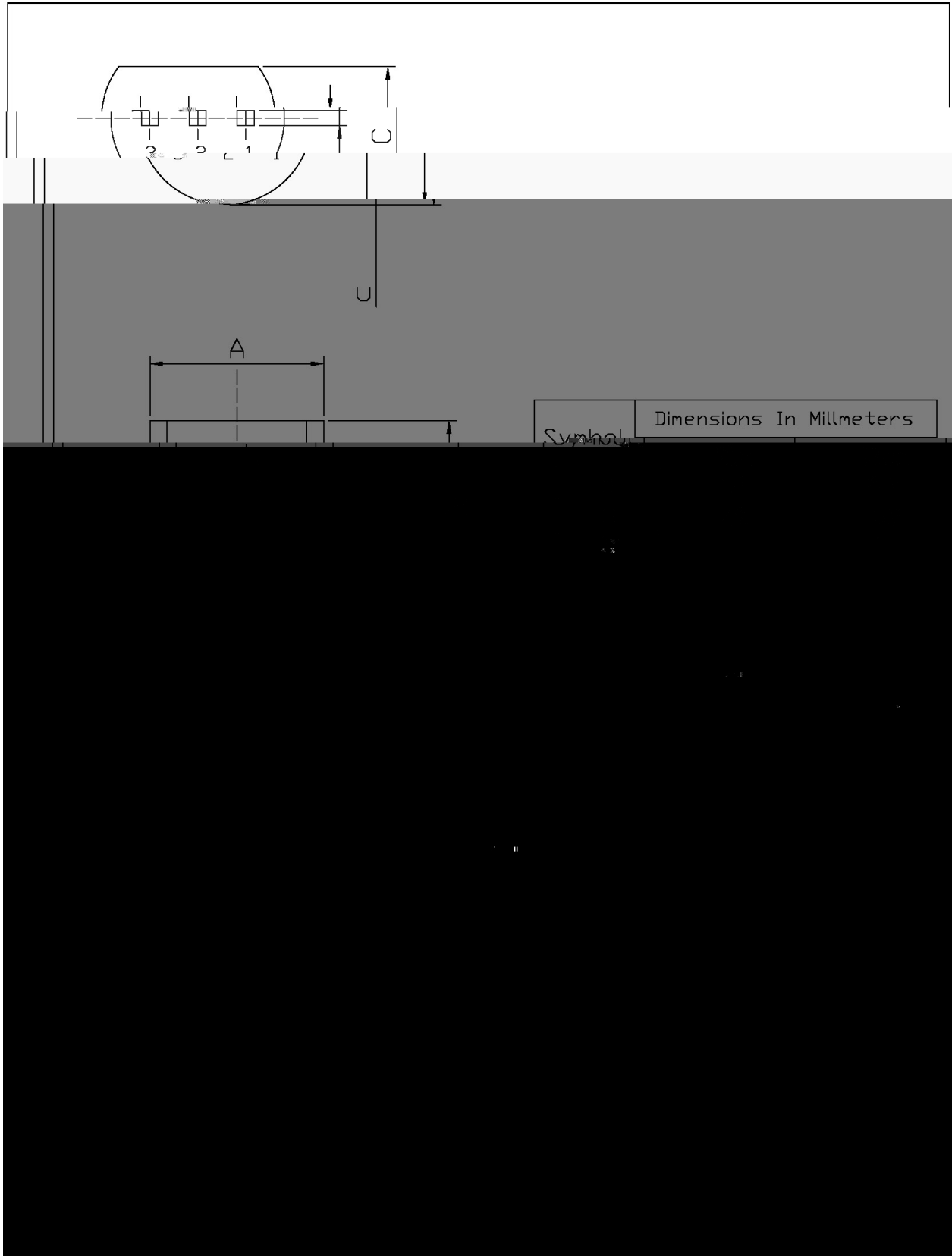
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-350	V
Collector to Emitter Voltage	V_{CEO}	-350	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Base Current - Continuous	I_B	-250	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

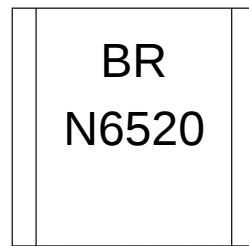
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-350			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-350			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -250V$ $I_E = 0$			-0.05	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4.0V$ $I_C = 0$			-0.05	μA



T0-92

Unit: mm



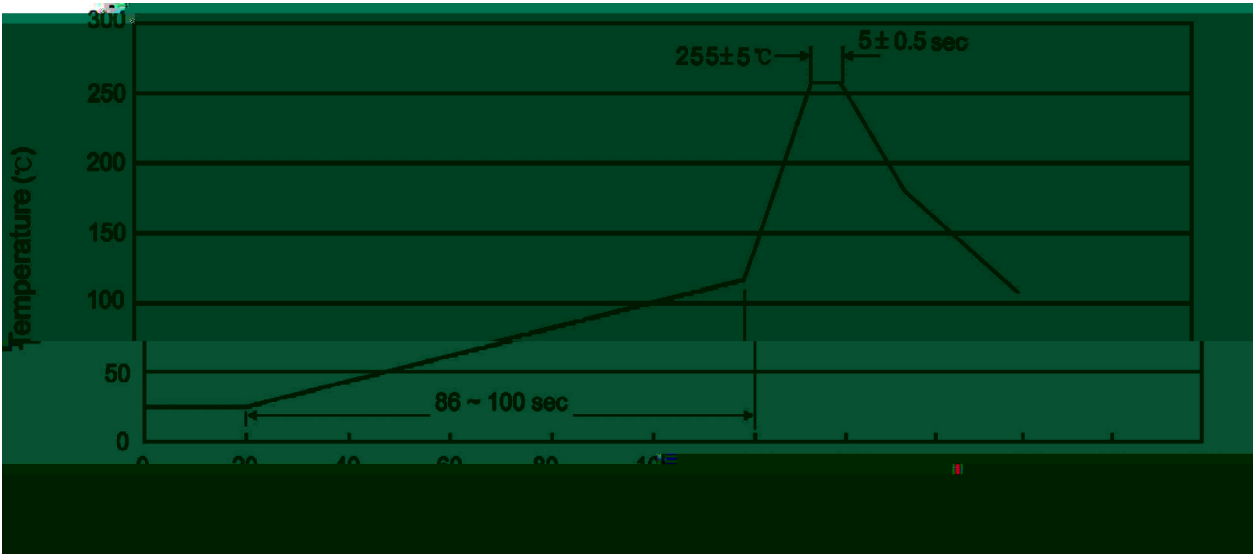


Note:

BR: Company Code.

N6520: Product Type.

****: Lot No. Code, code change with Lot No.



Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

270 5 10 1 sec. Temp.:270±5